

SOT-23 Plastic-Encapsulate Transistors

Features

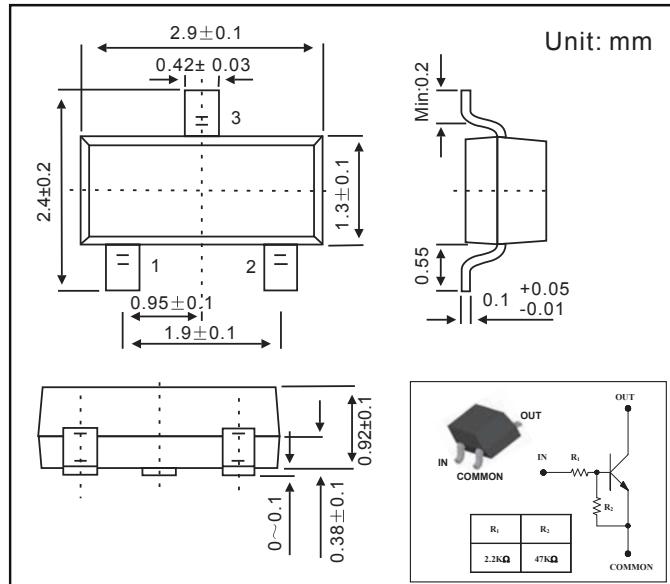
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- High packing density
- NPN Silicon Transistor

Descriptions

- Switching application
- Interface circuit and driver circuit application

MECHANICAL DATA

- Case: SOT-23 Small Outline Plastic Package
- Polarity: Color band denotes cathode end
- Mounting Position: Any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Characteristic	Symbol	Rating	Unit
Output voltage	V _O	50	V
Input voltage	V _I	15,-5	V
Output current	I _O	100	mA
Power dissipation	P _D	200	mW
Junction temperature	T _J	150	°C
Storage temperature range	T _{stg}	-55 ~ 150	°C

Electrical Specification (T_A=25°C unless otherwise specified)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Output cut-off current	I _{O(OFF)}	V _O =50V, V _I =0	-	-	500	nA
DC current gain	G _I	V _O =5V, I _O =10mA	80	200	-	-
Output voltage	V _{O(ON)}	I _O =10mA, I _I =0.5mA	-	0.1	0.3	V
Input voltage (ON)	V _{I(ON)}	V _O =0.2V, I _O =5mA	-	-	1.1	V
Input voltage (OFF)	V _{I(OFF)}	V _O =5V, I _O =0.1mA	0.5	-	-	V
Transition frequency	f _T [*]	V _O =10V, I _O =5mA, f=1MHz	-	200	-	MHz
Input current	I _I	V _I =5V, I _O =0	-	-	3.6	mA
Input resistor (Input to base)	R ₁	-	1.54	2.2	2.86	kΩ
Input resistor (Base to common)	R ₂	-	33	47	61	kΩ

* : Characteristic of transistor only

RATINGS AND CHARACTERISTIC CURVES

Fig. 1 P_D - T_a

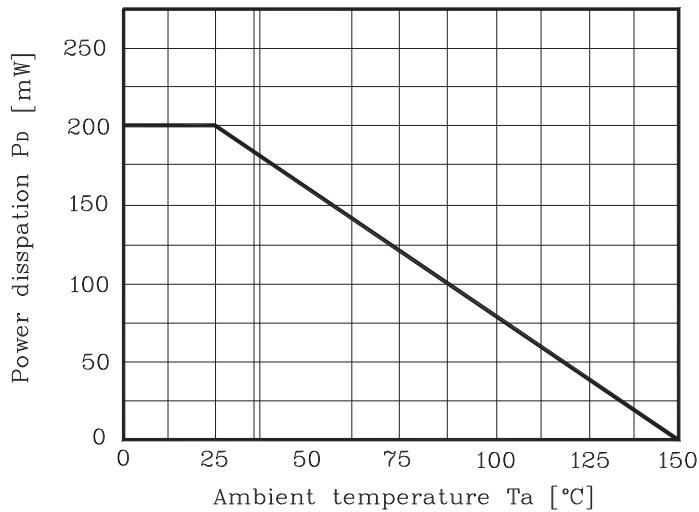


Fig. 2 I_O - $V_{I(ON)}$

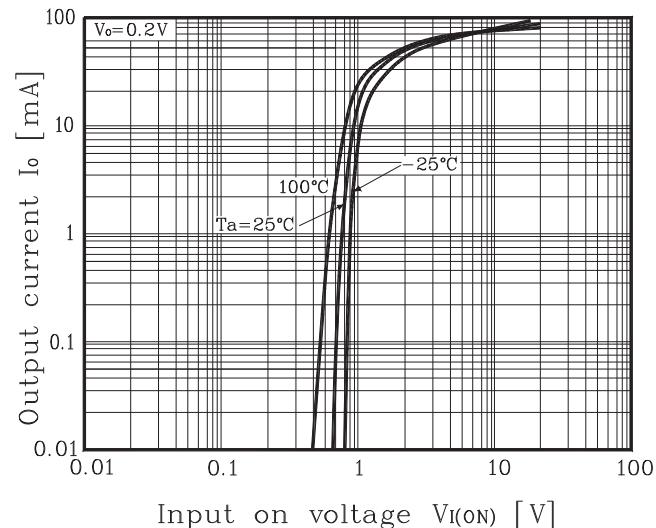


Fig. 3 I_O - $V_{I(OFF)}$

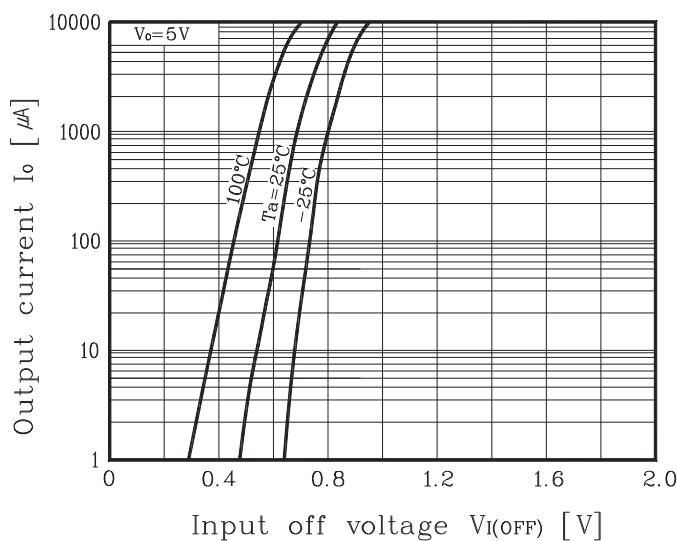


Fig. 4 G_I - I_O

